



# DATA SHEET

SEMICONDUCTOR

BC846 Thru BC850 Series

## General Purpose Transistors

**NPN Silicon**

**MAXIMUM RATINGS**

Rating	Symbol	BC847 BC848			Unit
		BC846	BC850	BC849	
Collector–Emitter Voltage	$V_{CE0}$	65	45	30	V
Collector–Base Voltage	$V_{CBO}$	80	50	30	V
Emitter–Base Voltage	$V_{EBO}$	6.0	6.0	5.0	V
Collector Current — Continuous	$I_C$	100	100	100	mAdc
Collector Current(Peak value)	$I_{CM}$	200	200	200	mAdc
Emitter Current(Peak value)	$I_{EM}$	200	200	200	mAdc
Base Current(Peak value)	$I_{BM}$	200	200	200	mAdc

### SOLDERING CHARACTERISTICS

Characteristic	Symbol	Unit
Solder Heat Resistance	265	°C
Solderability	240 to 265	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	°C

### DEVICE MARKING

BC846= 1A; BC846B = 1B; BC847A = 1E; BC847B = 1F; BC847C= 1G; BC848A= 1J; BC848B= 1K; BC848C= 1L; BC850C= 2G
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### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ )	BC846A,B	65	—	—	v
	BC847A,B,C, BC850B,C	$V_{(BR)CEO}$	45	—	
	BC848A,B,C, BC849B,C	30	—	—	
Collector–Emitter Breakdown Voltage ( $I_C = 10\ \mu\text{A}, V_{EB} = 0$ )	BC846A,B	80	—	—	v
	BC847A,B,C, BC850B,C	$V_{(BR)CES}$	50	—	
	BC848A,B,C, BC849B,C	30	—	—	
Collector–Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ )	BC846A,B	80	—	—	v
	BC847A,B,C, BC850B,C	$V_{(BR)CBO}$	50	—	
	BC848A,B,C, BC849B,C	30	—	—	
Emitter–Base Breakdown Voltage ( $I_E = 1.0\ \mu\text{A}$ )	BC846A,B BC847A,B,C	6.0	—	—	v
	BC848A,B,C, BC849B,C,	$V_{(BR)EBO}$	5.0	—	
	BC850B,C	5.0	—	—	
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ ) ( $V_{CB} = 30\text{ V}, T_A = 150^\circ\text{C}$ )		$I_{CBO}$	—	15	nA
			—	5.0	$\mu\text{A}$

1. FR–5 = 1.0 x 0.75 x 0.062 in

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

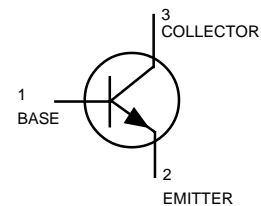
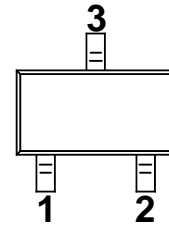
<http://www.yeashin.com>

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SOT–23 (TO–236AB)



# DEVICE CHARACTERISTICS

## BC846 Thru BC850 Series

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 10\ \mu\text{A}$ , $V_{CE} = 5.0\ \text{V}$ )	$h_{FE}$	—	90	—	—
		—	150	—	—
		—	270	—	—
( $I_C = 2.0\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ )		110	180	220	
		200	290	450	
		420	520	800	
Collector–Emitter Saturation Voltage ( $I_C = 10\ \text{mA}$ , $I_B = 0.5\ \text{mA}$ ) ( $I_C = 100\ \text{mA}$ , $I_B = 5.0\ \text{mA}$ )	$V_{CE(sat)}$	—	—	0.25 0.6	V
Base–Emitter Saturation Voltage ( $I_C = 10\ \text{mA}$ , $I_B = 0.5\ \text{mA}$ ) ( $I_C = 100\ \text{mA}$ , $I_B = 5.0\ \text{mA}$ )	$V_{BE(sat)}$	—	0.7 0.9	—	V
Base–Emitter Voltage ( $I_C = 2.0\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ ) ( $I_C = 10\ \text{mA}$ , $V_{CE} = 5.0\ \text{V}$ )	$V_{BE(on)}$	580	660	700 770	mV

### SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 10\ \text{mA}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $f = 100\ \text{MHz}$ )	$f_T$	100	—	—	MHz
Output Capacitance ( $V_{CB} = 10\ \text{V}$ , $f = 1.0\ \text{MHz}$ )	$C_{obo}$	—	—	4.5	pF
Noise Figure ( $I_C = 0.2\ \text{mA}$ , BC846A, BC847A, BC848A $V_{CE} = 5.0\ \text{Vdc}$ , $R_S = 2.0\ \text{k}\Omega$ , BC846B, BC847B, BC848B $f = 1.0\ \text{kHz}$ , $BW = 200\ \text{Hz}$ )	NF	—	—	10 4.0	dB

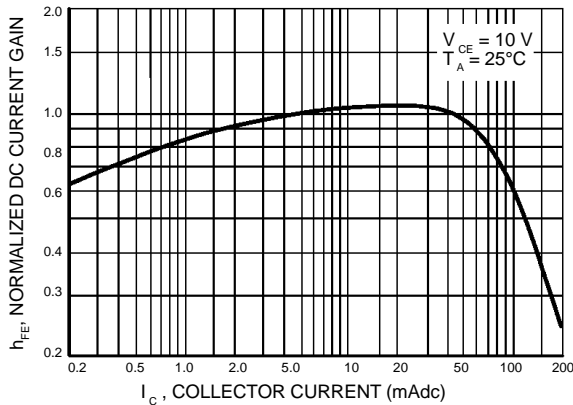


Figure 1. Normalized DC Current Gain

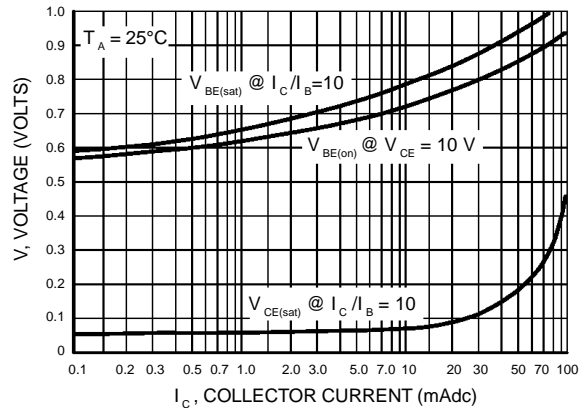


Figure 2. "Saturation" and "On" Voltages

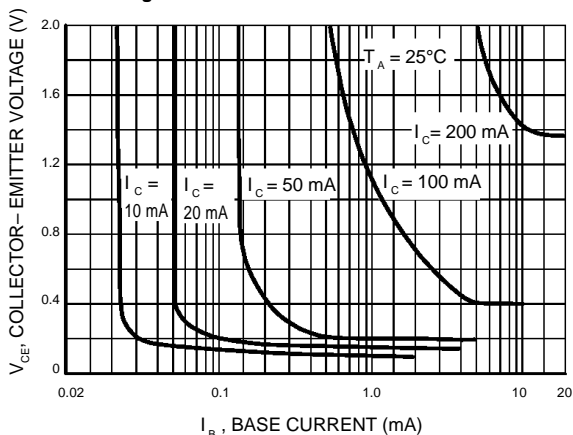


Figure 3. Collector Saturation Region

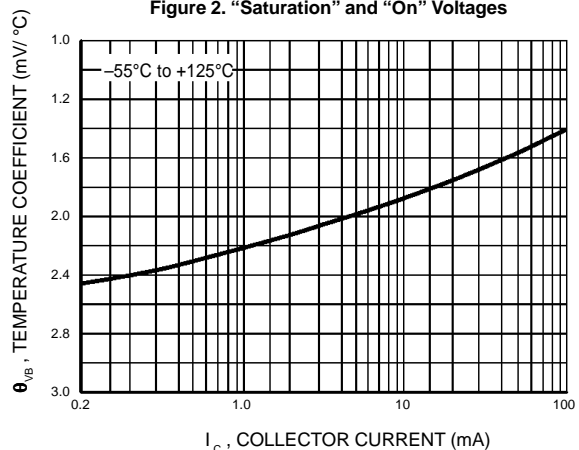


Figure 4. Base–Emitter Temperature Coefficient

# DEVICE CHARACTERISTICS

## BC846 Thru BC850 Series

### BC847/BC848

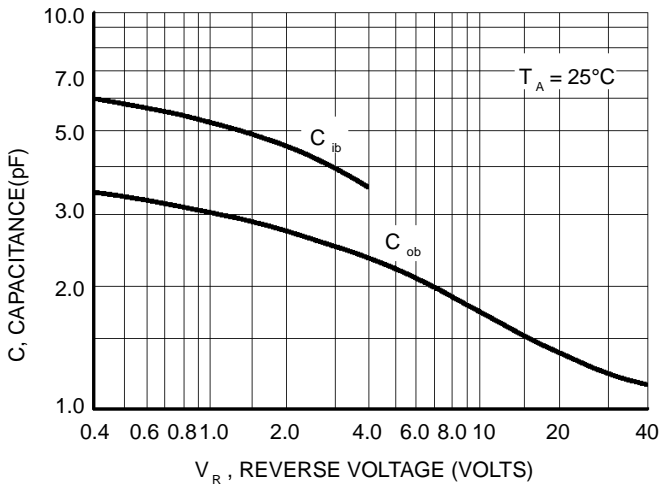


Figure 5. Capacitances

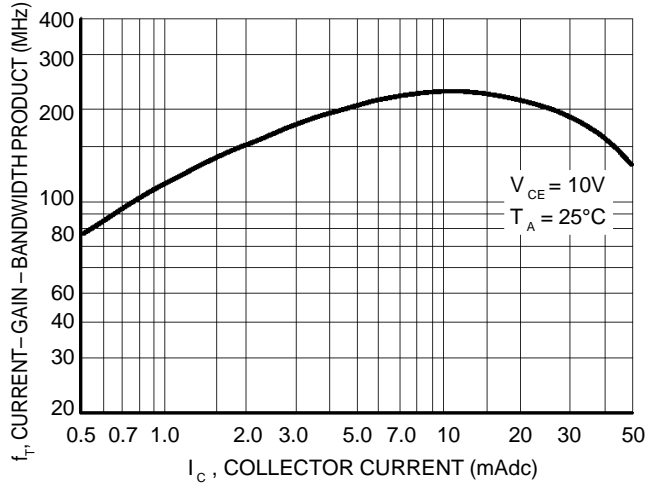


Figure 6. Current-Gain - Bandwidth Product

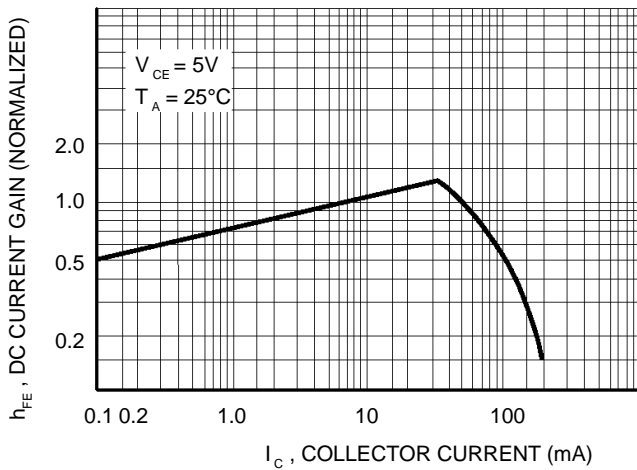


Figure 7. DC Current Gain

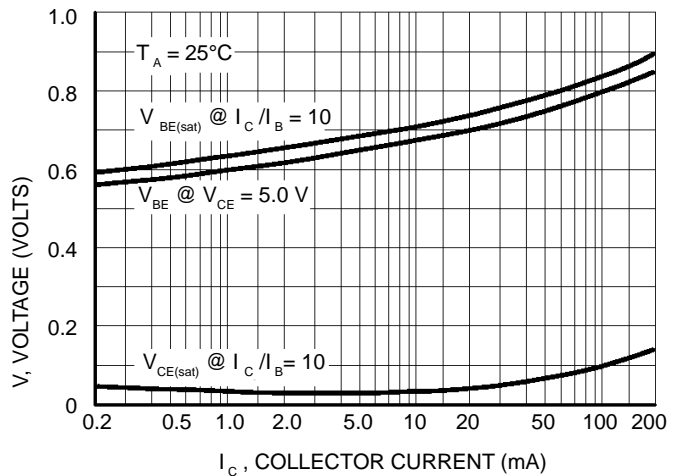


Figure 8. "On" Voltage

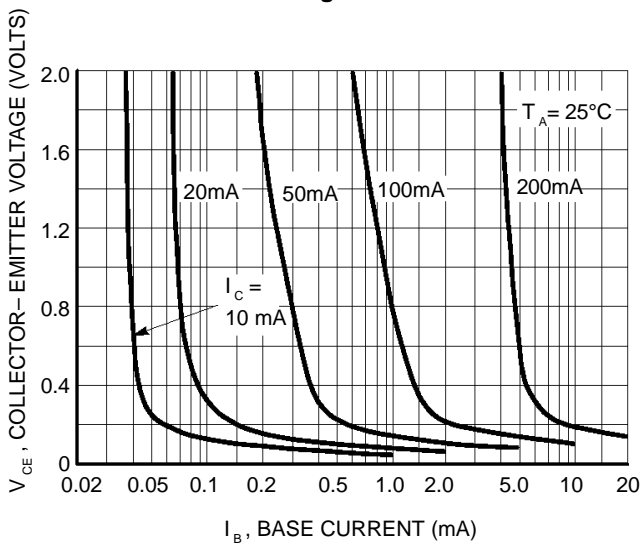


Figure 9. Collector Saturation Region

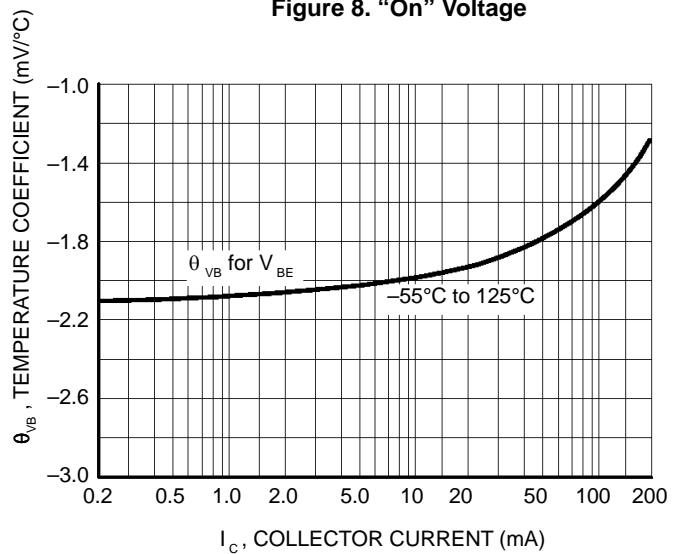


Figure 10. Base-Emitter Temperature Coefficient

# DEVICE CHARACTERISTICS

## BC846 Thru BC850 Series

### BC846

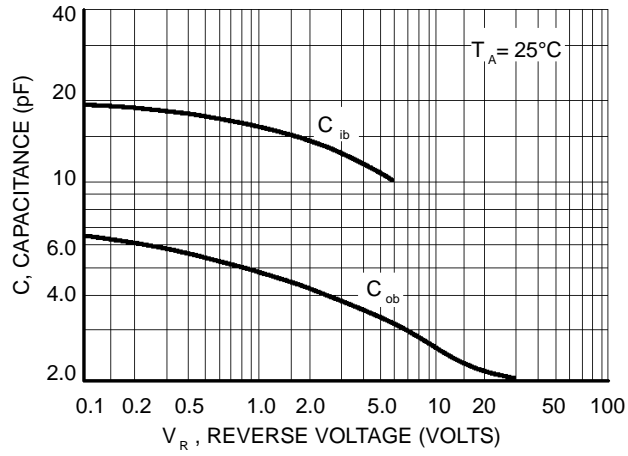


Figure 11. Capacitance

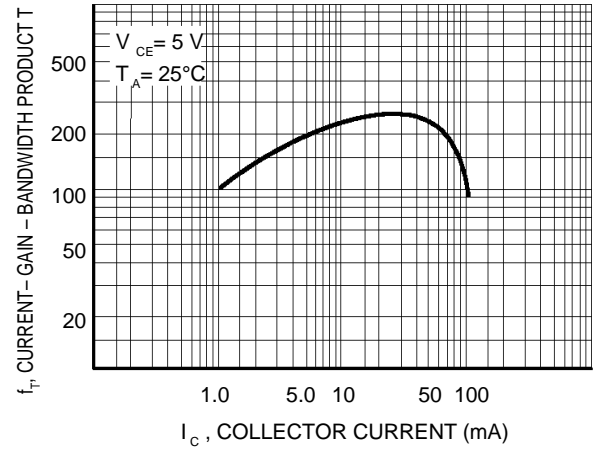


Figure 12. Current-Gain - Bandwidth Product

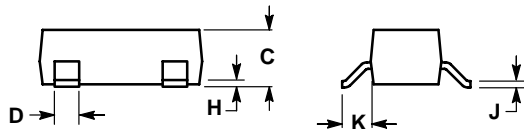
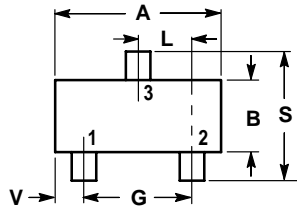
# PACKAGE OUTLINE & DIMENSIONS

## BC846 Thru BC850 Series

### SOT-23

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

